

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
400)/	160mΩ @ V _{GS} = 10V	2.6A
100V	$200 \text{m}\Omega$ @ $V_{GS} = 4.5V$	2.3A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

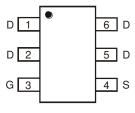
Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.015 grams (Approximate)

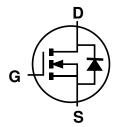
TSOT26



Top View



Top View Pin-Out



Equivalent Circuit

Ordering Information (Note 4)

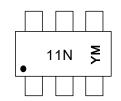
Part Number	Case	Packaging
DMN10H170SVT-7	TSOT26	3,000/Tape & Reel
DMN10H170SVT-13	TSOT26	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

TSOT26



11N = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	2014		2015	2016		2017	2018		2019	2020		2021
Code	В		С	D		Е	F		G	Н		l
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	100	V		
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			I _D	2.6 2.1	Α
Pulsed Drain Current (10µs pulse, duty cycle ≦1%)	I _{DM}	11.2	Α		
Maximum Body Diode Continuous Current (Note 6)	Is	2.0	A		

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Dawar Dissination	(Note 5)	Б	1.2	W	
Total Power Dissipation	(Note 6)	P _D	1.7	VV	
Thermal Resistance, Junction to Ambient	(Note 5)	Б	101		
memial nesistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	73	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	$R_{ heta JC}$	15		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

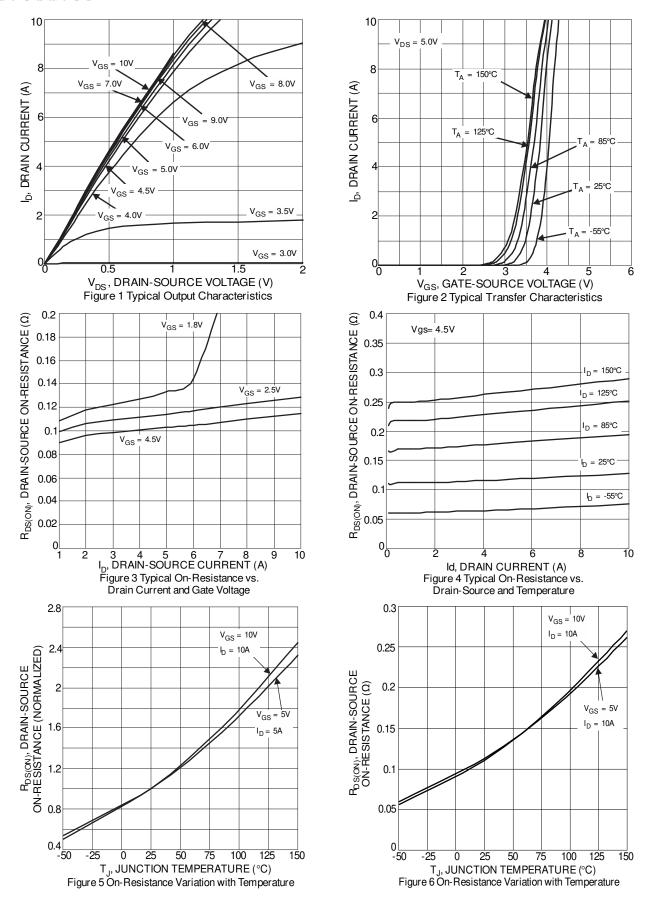
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	V _{DS} = 100V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.0	2.0	3.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	0	_	115	160	~ 0	$V_{GS} = 10V, I_D = 5.0A$
Static Drain-Source On-Resistance	R _{DS (ON)}	_	124	200	mΩ	$V_{GS} = 4.5V, I_D = 5.0A$
Diode Forward Voltage	V _{SD}	_	0.9	1.0	V	V _{GS} = 0V, I _S = 10A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	1,167	_		V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	_	36	_	рF	
Reverse Transfer Capacitance	C _{rss}	_	25	_		
Gate Resistance	R_g	_	1.3	_	Ω	VDS = 0V, $VGS = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	4.9	_		
Total Gate Charge (V _{GS} = 10V)	Qg	_	9.7		0	V 00V I 10 0A
Gate-Source Charge	Q _{gs}	_	2.0	_	nC	$V_{DS} = 80V, I_{D} = 12.8A$
Gate-Drain Charge	Q_{gd}	_	2.0	_		
Turn-On Delay Time	t _{D(on)}	_	10	_		
Turn-On Rise Time	t _r	_	11	_	0	$V_{DD} = 50V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(off)}	_	42	_	nS	$R_G = 25\Omega$, $I_D = 12.8A$
Turn-Off Fall Time	t _f	_	12	_		
Reverse Recovery Time	t _{rr}		30	_	nS	V 0V I- 10 0A di/d+ 100 A/··-
Reverse Recovery Charge	Q _{rr}	_	35		nC	$V_{GS} = 0V$, $I_{S}=12.8A$, $di/dt=100A/\mu s$

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

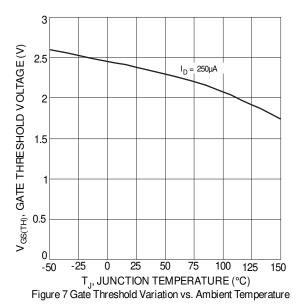
^{7.} Short duration pulse test used to minimize self-heating effect.

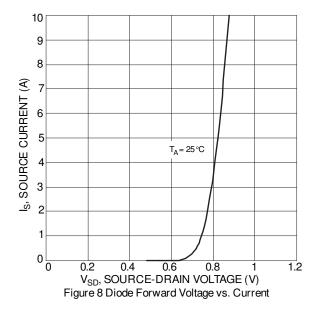
8. Guaranteed by design. Not subject to product testing.

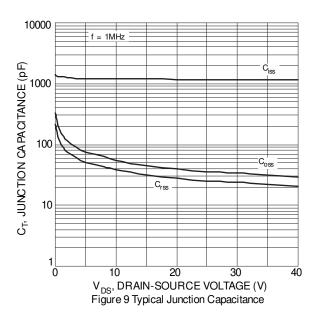


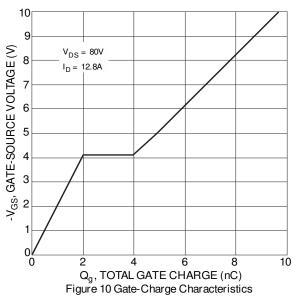


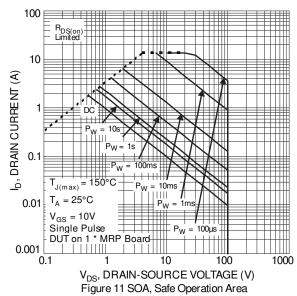




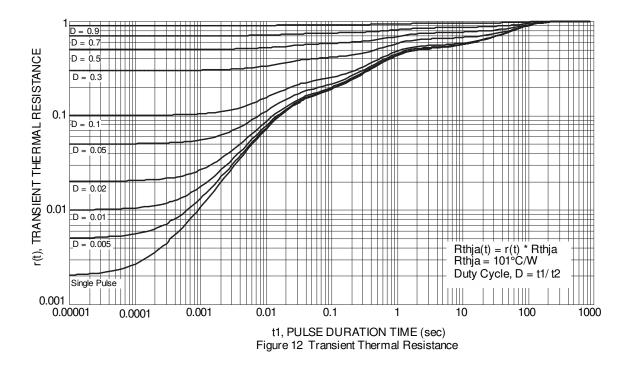






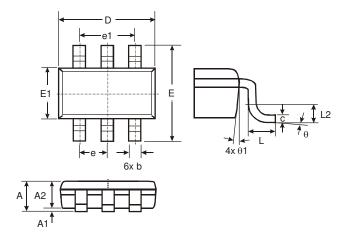






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

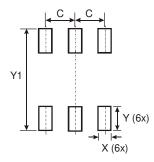


TSOT26							
Dim	Min	Max	Тур				
Α	ı	1.00	-				
A 1	0.01	0.10	_				
A2	0.84	0.90	_				
D	1	_	2.90				
П	-	_	2.80				
E1	ı	-	1.60				
q	0.30	0.45	_				
С	0.12	0.20	_				
е	1	_	0.95				
e1	-	_	1.90				
Г	0.30	0.50					
L2	I	_	0.25				
θ	0°	8°	4°				
θ1	4°	12°	_				
All Dimensions in mm							



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.950
Х	0.700
Υ	1.000
Y1	3.199

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